

General Description

The KSP4430 use advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

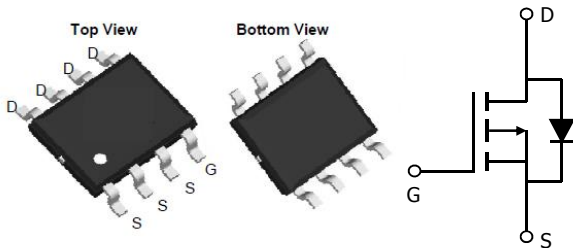
Product Summary

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)
-40	28 at $V_{GS} = 10$ V	-6.5
	33 at $V_{GS} = 4.5$ V	-5.3

Features

- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

SOP-8 Pin Configuration



Applications

- PWM applications
- Load switch
- Power management

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 25	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	-6.5	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	-4.0	A
I_{DM}	Drain Current – Pulsed ¹	-30	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	2.5	W
	Power Dissipation ($T_c=100^\circ\text{C}$)	0.05	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.94	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted) Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-40	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-25V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-25V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-4A$	---	28	36	$m\Omega$
		$V_{GS}=-4.5V, I_D=-3A$	---	33	42.6	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	-1.0	-1.7	-2.7	V
g_{fs}	Forward Transconductance	$V_{DS}=-15V, I_S=-3A$	---	30	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-10V, I_D=-3.5A$	---	21	---	nC
Q_{gs}	Gate-Source Charge		---	6.2	---	
Q_{gd}	Gate-Drain Charge		---	9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-15V, I_D=-2A$ $V_{GS}=-10V, R_G=3.3\Omega$	---	16	---	ns
T_r	Rise Time		---	8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	59	---	
T_f	Fall Time		---	14	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, F=1\text{MHz}$	---	1827	---	pF
C_{oss}	Output Capacitance		---	215	---	
C_{rss}	Reverse Transfer Capacitance		---	157	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-6.5	A
I_{SM}	Pulsed Source Current		---	---	-13	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^\circ\text{C}, V_{DD}=-15V, V_G=10V, L=0.5mH, R_G=25\Omega, I_{AS}=-34A$

Typical Electrical and Thermal Characteristics (Curves)

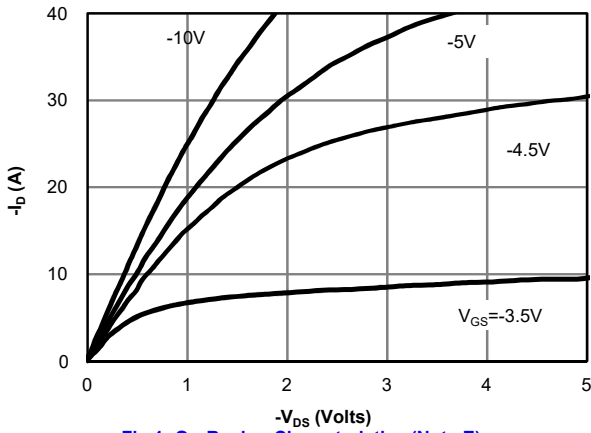


Fig 1: On-Region Characteristics (Note E)

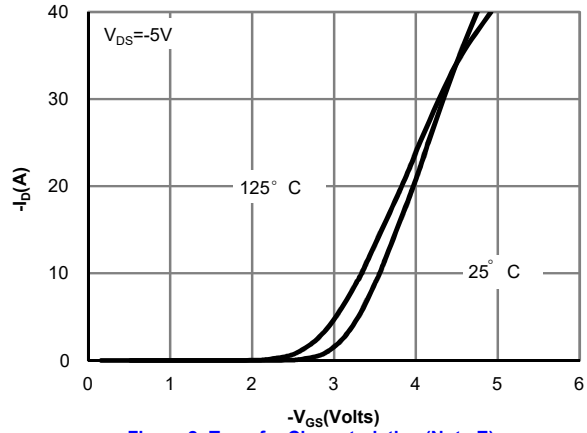


Figure 2: Transfer Characteristics (Note E)

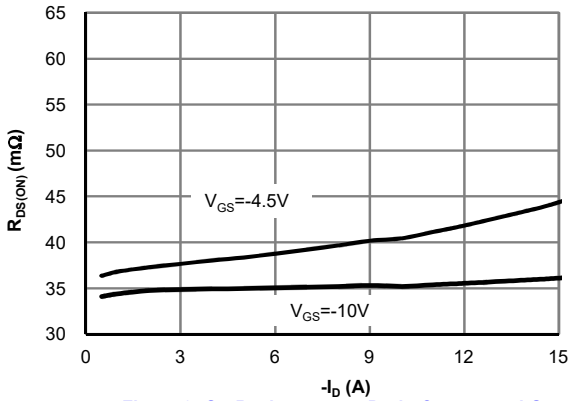


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

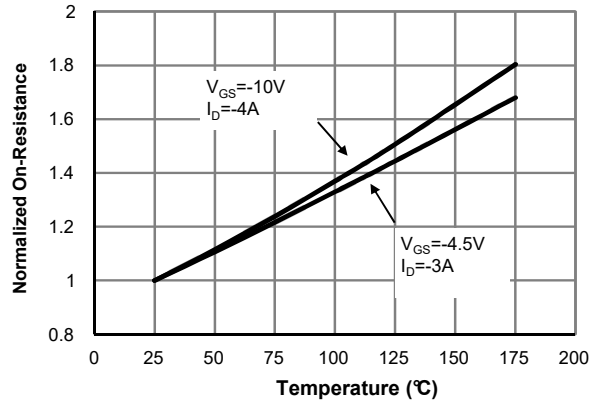


Figure 4: On-Resistance vs. Junction Temperature

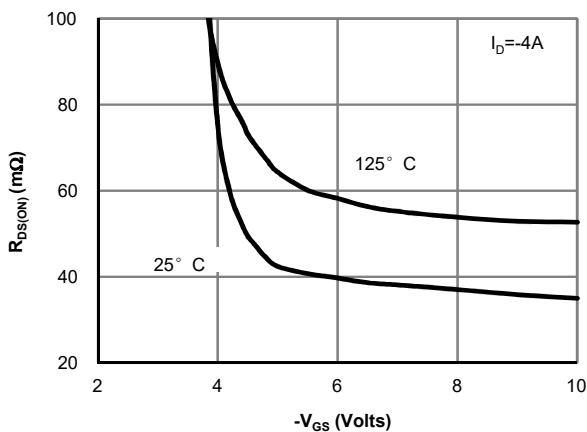


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

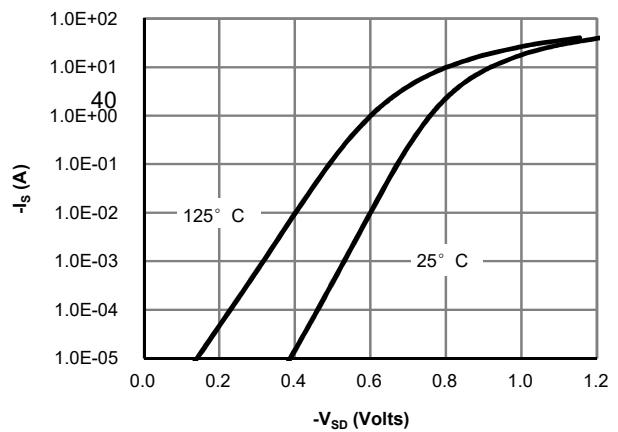


Figure 6: Body-Diode Characteristics (Note E)

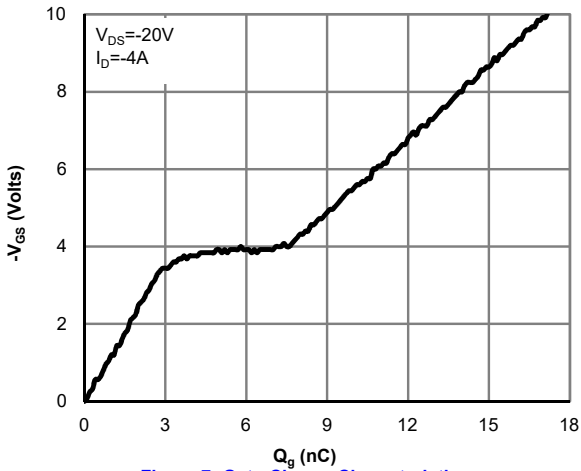


Figure 7: Gate-Charge Characteristics

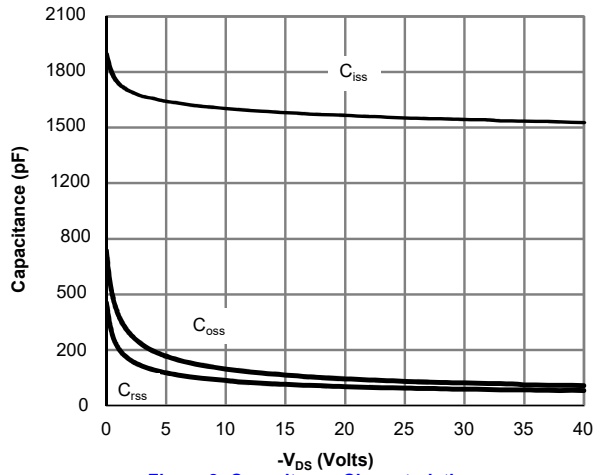


Figure 8: Capacitance Characteristics

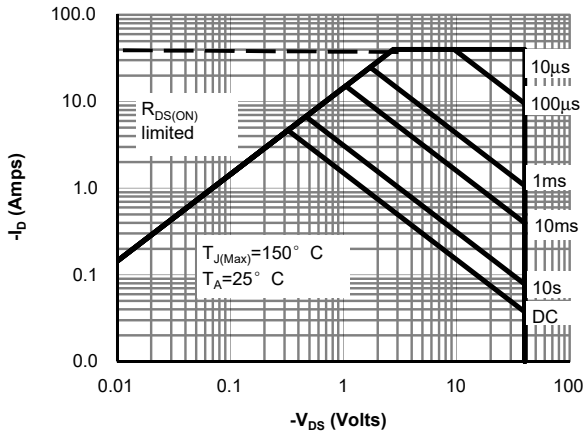


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

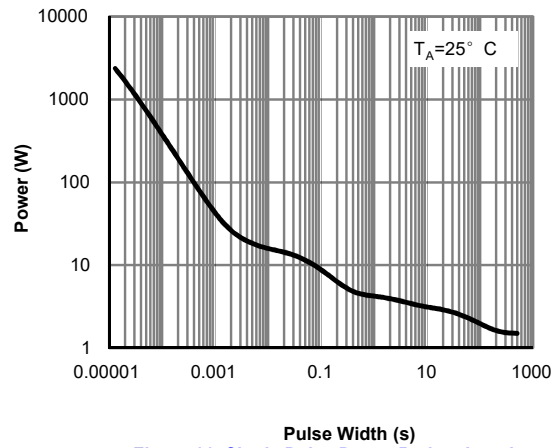


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

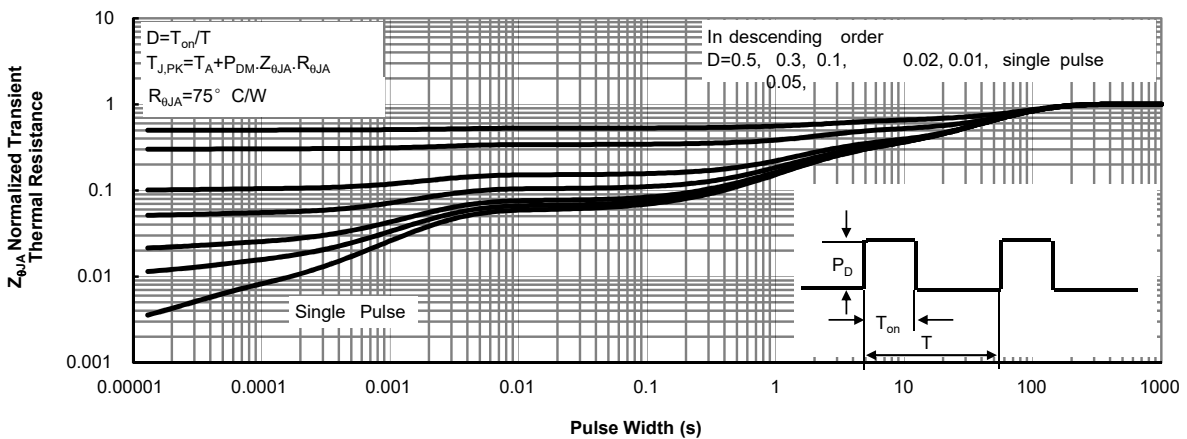


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

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